

SCOPE: LOW POWER FAST CMOS ANALOG SWITCHES

<u>Device Type</u>	<u>Generic Number</u>	<u>Circuit Function</u>
01	IH5148M(x)/883B	Two-channel, 30 Ω , SPST switch
02	IH5149M(x)/883B	Two-channel, 30 Ω , DPST switch
03	IH5150M(x)/883B	One-channel, 30 Ω , SPDT switch
04	IH5151M(x)/883B	Two-channel, 30 Ω , SPDT switch

Case Outline(s). The case outlines shall be designated in Mil-Std-1835 and as follows:

<u>Outline Letter</u>	<u>Mil-Std-1835</u>	<u>Case Outline</u>	<u>Package Code</u>
JE	GDIP1-T16 or CDIP2-T16	16 LEAD CERDIP	J16

Absolute Maximum Ratings:

V^+ to V^-	33V
V^+ to V_D	30V
V_D to V^-	30V
V_D to V_S	$\pm 22V$
V_L to V^-	33V
V_L to V_{IN}	30V
V_L to GND	20V
V_{IN} to GND	20V
V_R to V^-	33V
V_R to V_{IN}	2V
Continuous Current, Any terminal (except S or D)	30mA
Peak Current, S or D (Pulsed at 1ms, 10% duty cycle max)	80mA
Lead Temperature (soldering, 10 seconds)	+300°C
Storage Temperature	-65°C to +150°C
Continuous Power Dissipation	$T_A = +70^\circ C$
16 lead CERDIP (derate 10.0mW/°C above +70°C)	800mW
Junction Temperature T_J	+150°C
Thermal Resistance, Junction to Case, θ_{JC} :	
Case Outline 16 lead CERDIP.....	50°C/W
Thermal Resistance, Junction to Ambient, θ_{JA} :	
Case Outline 16 lead CERDIP.....	100°C/W

Recommended Operating Conditions

Ambient Operating Range (T_A)	-55°C to +125°C
Positive Supply Voltage (V^+)	+15V
Negative Supply Voltage (V^-)	-15V
V_R	0V
V_L	5V

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TABLE 1. ELECTRICAL TESTS:

TEST	Symbol	CONDITIONS -55 °C ≤ T _A ≤ +125°C V ⁺ =+15V, V ⁻ = -15V, GND=0V V _{AH} =2.4V, V _{AL} =0.8V, V _L =5V Unless otherwise specified	Group A Subgroup	Device type	Limits Min	Limits Max	Units
INPUT							
Input Current, Input Voltage High	I _{IH}	V _{IN} =2.4V, 5V	1,3 2	All	-1 -1	1 10	μA
Input Current, Input Voltage Low	I _{IL}	V _{IN} =0.0V	1,3 2	All	-1 -10	1 1	μA
SWITCH							
Drain-Source ON Resistance	r _{DS(ON)}	I _S = ±10mA, V _S = ±10V,	1,3 2	All		45 50	Ω 1/
Drain-Source ON Resistance	r _{DS(ON)}	I _S = ±10mA, V _D = ±7.5V, NOTE 2 V _{CC} = ±10V	1,3 2	All		75 150	Ω
Source- OFF Leakage Current	I _{S(OFF)}	V _S = ±10V, V _D = ±10V, V _{IN} = 3/	1 2,3	All		±1 ±100	nA
Drain- OFF Leakage Current	I _{D(OFF)}	V _S = ±10V, V _D = ±10V, V _{IN} = 3/	1 2,3	All		±1 ±100	nA
Channel-On Leakage Current	I _{D(ON)}	V _D = V _S = ±10V, V _{IN} = 3/	1 2,3	All		±2 ±200	nA
SUPPLY							
Positive Supply Current	I ⁺	V _{IN} = 0V, 5V	1 2,3	All		200 300	μA
Negative Supply Current	I ⁻	V _{IN} = 0V, 5V	1 2,3	All	-200 -300		μA
Logic Supply Current	I _L ⁺	V _{IN} = 0V, 5V	1 2,3	All		-200 -300	μA
Reference Supply Current	I _R	V _{IN} = 0V, 5V	1 2,3	All	-200 -300		μA
Turn-On Time	t _{ON}	Figure 1	9 10 11	All		500 800 450	ns
Turn-Off Time	t _{OFF}	Figure 1	9 10 11	All		450 600 350	ns
Single channel Isolation	V _{ISO}	R _L = 100Ω, f = 100kHz, V _{IN} = 2Vp-p, CL = 5pF, NOTE 2	9	All	60		dB
Crosstalk between channel	V _{CT}	R _L = 100Ω, f = 100kHz, V _{IN} = 2Vp-p, CL = 5pF, NOTE 2	9	All	60		dB
Charge Transfer Error	VCTE	V _{IN} = 0V, C _L = 10nF, NOTE 2	9	All		30	mV
Driver Input Capacitance	CA	V _{IN} = 0V, NOTE 2	9	All		45	pF
Switch Input Capacitance	CIS	Switch Off, NOTE 2	9	All		60	pF
Switch Output Capacitance	COS	Switch Off, NOTE 2	9	All		60	pF

NOTE 1: The listed resistance limits correspond to the following voltage values:

45Ω and 75Ω = ±9.25V, ±6.75V

50Ω and 150Ω = ±8.55V, ±6.0V

NOTE 2: Guaranteed if not tested to the limits specified.

NOTE 3:

Device Types	V _{IN}	Channels ON	Channels OFF
01	2.4V 0.8V	1, 2 3, 4	3, 4 1, 2
03	2.4V 0.8V	2, 3 1, 4	1,4 2,3
02, 04	2.4V 0.8V	1, 2, 3, 4	1, 2, 3, 4

Figure 1. Switching Time: See Commercial Data Sheet.

TERMINAL CONNECTIONS

TERMINAL NUMBER	03 IH5150	04 IH5151	02 IH5149	01 IH5148
0	J16	J16	J16	J16
1	D1	D1	D1	D1
2				
3	D2	D3	D3	
4	S2	S3	S3	
5		S4	S4	
6		D4	D4	
7				
8		D2	D2	D2
9		S2	S2	S2
10		IN2	IN2	IN2
11	V+	V+	V+	V+
12	VL	VL	VL	VL
13	VR	VR	VR	VR
14	V-	V-	V-	V-
15	IN	IN1	IN1	IN1
16	S1	S1	S1	S1

ORDERING INFORMATION

Device Type

Generic Number

Circuit Function

01	IH5148MJE/883B
02	IH5149MJE/883B
03	IH5150MJE/883B
04	IH5151MJE/883B

Two Channel, 30Ω SPST
Two Channel, 30Ω DPST
One Channel, 30Ω SPDT
Two Channel, 30Ω Dual SPDT

QUALITY ASSURANCE

Sampling and inspection procedures shall be in accordance with MIL-Prf-38535, Appendix A as specified in Mil-Std-883.

Screening shall be in accordance with Method 5004 of Mil-Std-883. Burn-in test Method 1015:

1. Test Condition, A, B, C, or D.
2. TA = +125°C minimum.
3. Interim and final electrical test requirements shall be specified in Table 2.

Quality conformance inspection shall be in accordance with Method 5005 of Mil-Std-883, including Groups A, B, C, and D inspection.

Group A inspection:

1. Tests as specified in Table 2.
2. Selected subgroups in Table 1, Method 5005 of Mil-Std-883 shall be omitted.

Group C and D inspections:

- a. End-point electrical parameters shall be specified in Table 1.
- b. Steady-state life test, Method 1005 of Mil-Std-883:
 1. Test condition A, B, C, D.
 2. TA = +125°C, minimum.
 3. Test duration, 1000 hours, except as permitted by Method 1005 of Mil-Std-883.

TABLE 2. ELECTRICAL TEST REQUIREMENTS

Mil-Std-883 Test Requirements	Subgroups per Method 5005, Table 1
Interim Electric Parameters Method 5004	1
Final Electrical Parameters Method 5005	1*, 2, 3
Group A Test Requirements Method 5005	1, 2, 3, 9, 10, 11
Group C and D End-Point Electrical Parameters Method 5005	1

* PDA applies to Subgroup 1 only.